



General Description

The ZM060N08HD combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

Features

- Trench technology
- $R_{DS(ON)}$ to minimize conductive loss
- fast switching

Application

- nd Synchronous Rectifier
- Switching application

Product Summary



$V_{DS} = 80V$

$R_{DS(ON)} = 6.2m\Omega$

$I_D = 60A$



Ordering Information:

Part NO.	ZM060N08HD
Marking	ZM060N08H
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

Absolute Maximum Ratings $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	60	A
	$I_{D@TC=75}$	45	A
	$I_{D@TC=100}$	38	A
Pulsed Drain Current	I_{DM}	180	A
Total Power Dissipation	$P_D@TC=25$	60	W
Total Power Dissipation	$P_D@TA=25$	2.0	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy @L=0.5mH	E_{AS}	840	mJ



Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
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Unit mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			

